



PNP MJ4030 – MJ4031 – MJ4032

MEDIUM POWER COMPLEMENTARY SILICON TRANSISTORS

They are silicon epitaxial-base PNP power transistors in monolithic Darlington configuration and are mounted in Jedec TO-3 metal case.
 They are intended for use as output devices in complementary general purpose amplifier applications.
 The complementary NPN types are the MJ4033, MJ4034, MJ4035
 Compliance to RoHS

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings			Value	Unit
V _{CBO}	Collector-Base Voltage	I _E =0	MJ4030	-60	V
			MJ4031	-80	
			MJ4032	-100	
V _{CEO}	Collector-EmitterVoltage	I _B =0	MJ4030	-60	V
			MJ4031	-80	
			MJ4032	-100	
V _{EBO}	Emitter-Base Voltage	I _C =0	MJ4030	-5.0	V
			MJ4031		
			MJ4032		
I _C	Collector Current			-16	A
I _B	Base Current			-0.5	A
P _T	Power Dissipation	@ T _C < 25°		150	W
T _J	Junction Temperature			200	℃
T _s	Storage Temperature			-65 to +200	

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-C}	Thermal Resistance, Junction to Case	1.17	$^\circ\text{C/W}$

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

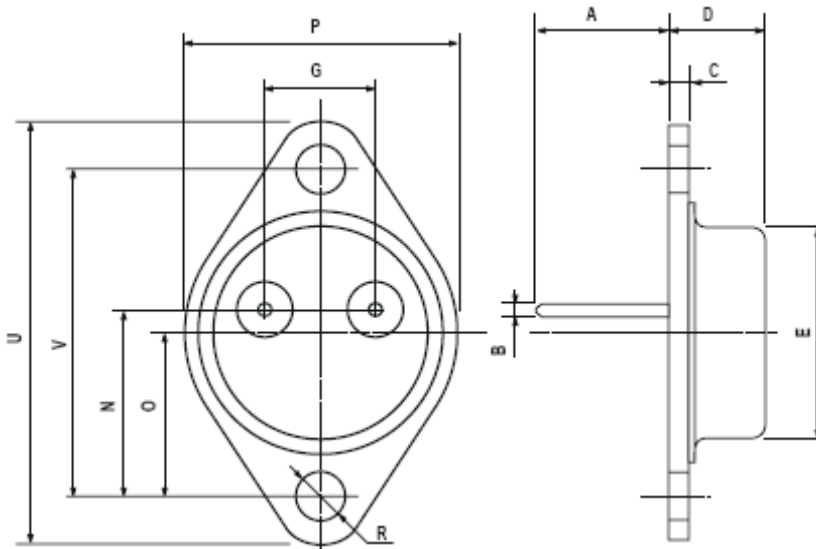
Symbol	Ratings	Test Condition(s)		Min	Typ	Max	Unit
V_{CEO}	Collector-Emitter Voltage (*)	$I_C=-100\text{ mA}$, $I_B=0$	MJ4030	-60	-	-	V
			MJ4031	-80	-	-	
			MJ4032	-100			
I_{CEO}	Collector Cutoff Current	$V_{CE}=-30\text{ Vdc}$, $I_B=0$	MJ4030	-	-	-3.0	mA
		$V_{CE}=-40\text{ Vdc}$, $I_B=0$	MJ4031	-	-		
		$V_{CE}=-50\text{ V}$, $I_B=0$	MJ4032	-	-		
I_{EBO}	Emitter Cutoff Current	$V_{BE}=-5.0\text{ V}$, $I_C=0$	MJ4030	-	-	-5.0	mA
			MJ4031				
			MJ4032				
I_{CER}	Collector-Emitter Leakage Current	$V_{CB}=-60\text{ V}$ $R_{BE}=1.0\text{ k}\Omega$	MJ4030	-	-	-1.0	mA
		$V_{CB}=-80\text{ V}$ $R_{BE}=1.0\text{ k}\Omega$	MJ4031	-	-		
		$V_{CB}=-100\text{ V}$ $R_{BE}=1.0\text{ k}\Omega$	MJ4032				
		$V_{CB}=-60\text{ V}$ $R_{BE}=1.0\text{ k}\Omega$ $T_C=150^{\circ}\text{C}$	MJ4030	-	-	-5.0	
		$V_{CB}=-80\text{ V}$ $R_{BE}=1.0\text{ k}\Omega$ $T_C=150^{\circ}\text{C}$	MJ4031	-	-		
		$V_{CB}=-100\text{ V}$ $R_{BE}=1.0\text{ k}\Omega$ $T_C=150^{\circ}\text{C}$	MJ4032				
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C=-10\text{ A}$ $I_B=-40\text{ mA}$	MJ4030	-	-	-2.5	V
			MJ4031				
			MJ4032				
		$I_C=-16\text{ A}$ $I_B=-80\text{ mA}$	MJ4030	-	-	-4.0	
			MJ4031				
			MJ4032				
V_{BE}	Base-Emitter Voltage (*)	$I_C=-10\text{ A}$ $V_{CE}=-3.0\text{V}$	MJ4030	-	-	-3	V
			MJ4031				
			MJ4032				
h_{FE}	DC Current Gain (*)	$V_{CE}=-10\text{ V}$ $I_C=-3.0\text{ A}$	MJ4030	1000	-	-	-
			MJ4031				
			MJ4032				

(*) Pulse Width $\approx 300 \mu\text{s}$, Duty Cycle $\angle 2.0\%$

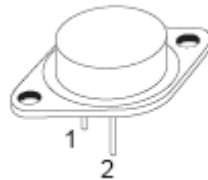
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MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)		
	min	max
A	11	13.10
B	0.97	1.15
C	1.5	1.65
D	8.32	8.92
F	19	20
G	10.70	11.1
N	16.50	17.20
P	25	26
R	4	4.09
U	38.50	39.30
V	30	30.30



Pin 1 :	Base
Pin 2 :	Emitter
Case :	Collector



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